# FAIRCHILD

SEMICONDUCTOR®

# **KSC5042F**

# High Voltage Switchihg Dynamic Focus Application

- High Collector-Emitter Breakdown Voltage : BV<sub>CEO</sub>=900V
- Small C<sub>ob</sub> =2.8pF (Typ.)
  Wide S.O.A
- High reliability



KSC5042F

1.Base 2.Collector 3.Emitter

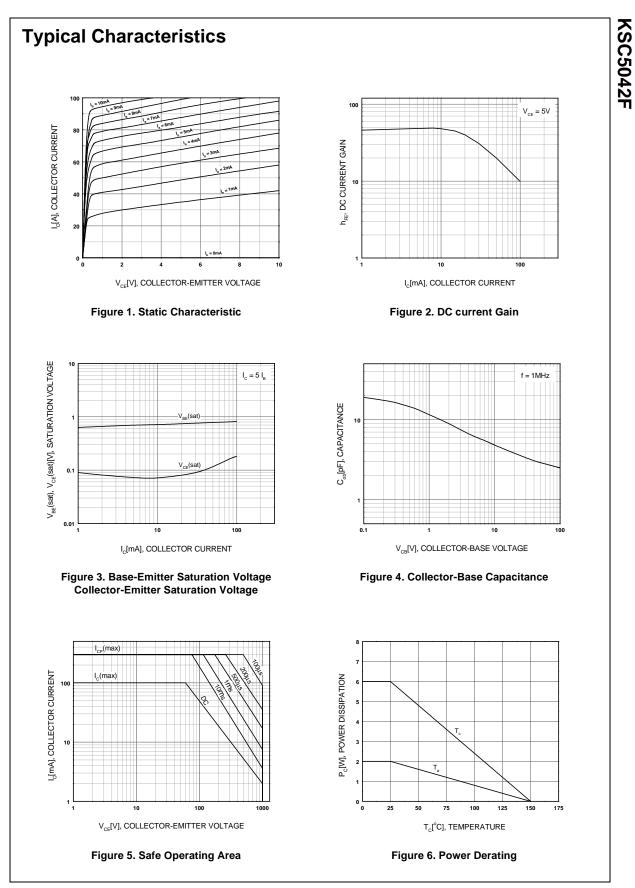
# NPN Triple Diffused Planar Silicon Transistor

# Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value		
V <sub>CBO</sub>	Collector-Base Voltage	1500	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	900	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5		
I <sub>C</sub>	Collector Current (DC)	100		
I <sub>CP</sub>	Collector Current (Pulse)	300	mA	
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	6	W	
TJ	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C	

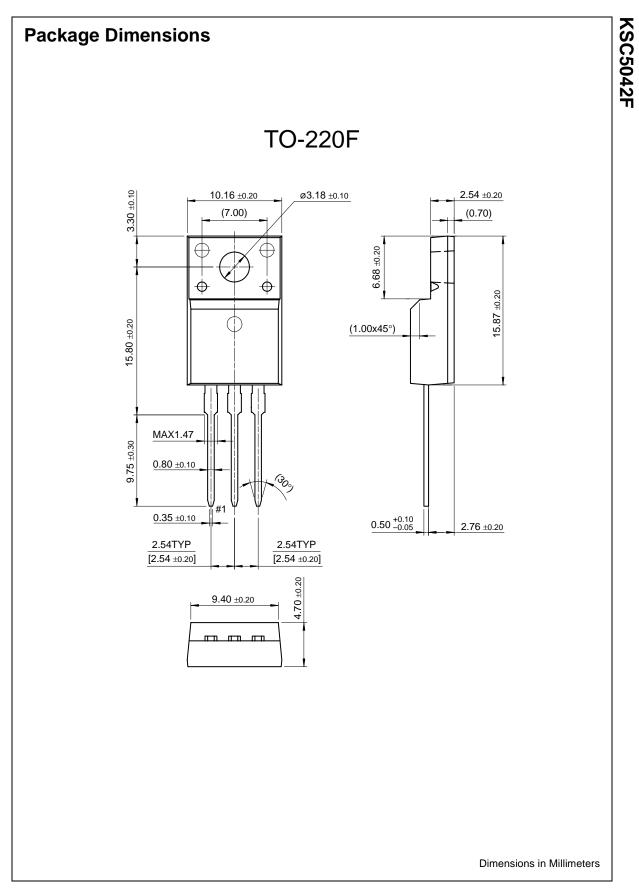
# Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition		Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = 1 m A, I_{E} = 0$	1500			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 5 {\rm mA}, I_{\rm B} = 0$	900			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_{E} = 1 \text{mA}, I_{C} = 0$	5			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 900V, I_E = 0$			10	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 4V, I_{C} = 0$			10	μΑ
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 5V, I_{C} = 10mA$	30			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_{\rm C} = 20 {\rm mA}, I_{\rm B} = 4 {\rm mA}$			5	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_{\rm C} = 20 {\rm mA}, I_{\rm B} = 4 {\rm mA}$			2	V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 100V, f = 1MHz		2.8		pF



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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

## **PRODUCT STATUS DEFINITIONS**

#### **Definition of Terms**

Datasheet Identification	Product Status	Definition				
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.				
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.				
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.				
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.				



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# **KSC5042F**

NPN Triple Diffused Planar Silicon Transistor

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## Features

- High Collector-Emitter Breakdown Voltage: BV<sub>CEO</sub>=900V
- Small C<sub>ob</sub>=2.8pF (Typ.)
- Wide S.O.A.
- High reliability

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Applications

**High Voltage Switching Dynamic Focus** 

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Product status/pricing/packaging



Product	Product status	Pb-free Status	Pricing*	Package type	Leads	Packing method	Package Marking Convention**	
KSC5042FTU	Full Production	Full Production	\$0.372	<u>TO-220F</u>	3		<u>Line 1:</u> <b>\$Y</b> (Fairchild logo) <u>Line 2:</u> C5042F <u>Line 3:</u> &3	
KSC5042FYDTU	Full Production	Full Production	\$0.372	<u>TO-220F</u>	3		Line 1: <b>\$Y</b> (Fairchild logo) Line 2: C5042F Line 3: &3	

# **Related Links**

Request samples

How to order products

Product Change Notices (PCNs)

Support

Sales support

Quality and reliability

Design center

\* Fairchild 1,000 piece Budgetary Pricing \*\* A sample button will appear if the part is available through Fairchild's on-line samples program. If there is no sample button, please contact a Fairchild distributor to obtain samples

Ø Indicates product with Pb-free second-level interconnect. For more information click here.

Package marking information for product KSC5042F is available. Click here for more information .

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## **Qualification Support**

Click on a product for detailed qualification data

Product
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KSC5042FYDTU

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